

IPD320N20N3GBTMA1

IPD320N20N3GBTMA1 Information



For Reference Only

Part Number IPD320N20N3GBTMA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V 34A TO252-3 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPD320N20N3GBTMA1 Specifications

Manufacturer Part Number IPD320N20N3GBTMA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 34A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 90μA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2350pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-T0252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
Category Discrete Semiconductor Products Fackage Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 34A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 90μA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2350pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IPD320N20N3GBTMA1
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SeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C34A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 90μAGate Charge (Qg) (Max) @ Vgs29nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2350pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)136W (Tc)Rds On (Max) @ Id, Vgs32 mOhm @ 34A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) 200V Current - Continuous Drain (Id) @ 25°C 34A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature Joperating Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case NaA (Tc) MOUNTING Ada (Tc) 34A (Tc) 34B (T	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C34A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 90μAGate Charge (Qg) (Max) @ Vgs29nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2350pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)136W (Tc)Rds On (Max) @ Id, Vgs32 mOhm @ 34A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	OptiMOS?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature Surplier Device Package PG-TO252-3 Package / Case 34A (Tc) 4V @ 90μA 2350pF @ 100V 2350pF @ 100	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 90μA 29nC @ 10V 2350pF @ 100V 2350pF @ 100V 136W (Tc) 32mOhm @ 34A, 10V -55°C ~ 175°C (TJ) Surface Mount PG-TO252-3 TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	34A (Tc)
Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2350pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case 2350pF @ 100V 240V 50V 50V 50V 50V 50V 50V 50V	Vgs(th) (Max) @ Id	4V @ 90μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)136W (Tc)Rds On (Max) @ Id, Vgs32 mOhm @ 34A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	29nC @ 10V
FET Feature - Power Dissipation (Max) 136W (Tc) Rds On (Max) @ Id, Vgs 32 mOhm @ 34A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	2350pF @ 100V
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Rds On (Max) @ Id, Vgs32 mOhm @ 34A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	136W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	32 mOhm @ 34A, 10V
Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
· · · · · · · · · · · · · · · · · · ·	Supplier Device Package	PG-TO252-3
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IPD320N20N3GBTMA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPD320N20N3GBTMA1 Payment Methods



















IPD320N20N3GBTMA1 Shipping Methods













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